

Dielectric characterisation of ceramics from the TiO_2 – TeO_2 system

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Abstract

Compositions from TiO_2 – TeO_2 tie line were characterised using X-ray powder diffraction (XRD), scanning electron microscopy (SEM), transmission electron microscopy (TEM) and dilatometry. Results show that the only binary compound existing on the tie line is TiTe_3O_8 . Single-phase TiTe_3O_8 was synthesised at 700°C in air and sintered at 720°C to $\sim 95\%$ of theoretical density. Such ceramics exhibit a relative permittivity of 50, a $Q \times f$ -value of 30,600 GHz and a temperature coefficient of resonant frequency (τ_f) of $+133 \text{ ppm}/^\circ\text{C}$, measured at $\sim 5 \text{ GHz}$. The concentration of structural defects in the TiTe_3O_8 grains is negligible which makes the dielectric properties of TiTe_3O_8 ceramics insensitive to variations in the heat-treatment conditions. The TiTe_3O_8 compound is chemically compatible with TeO_2 , which displays a negative temperature coefficient of resonant frequency (a relative permittivity of 19.3, a $Q \times f$ -value of 30,000 GHz and a temperature coefficient of resonant frequency of $-119 \text{ ppm}/^\circ\text{C}$ for TeO_2 ceramics with $\sim 20\%$ porosity) and can be used for compensation of the temperature coefficient of resonant frequency of the TiTe_3O_8 compound. Ceramics from the TiTe_3O_8 – TeO_2 subsystem can be sintered to $>97\%$ of theoretical density at temperatures as low as 670°C , which together with the fact that the ceramics exhibit a highly tunable τ_f , relative permittivity around 30 and a $Q \times f$ -value of $\sim 22,000 \text{ GHz}$ suggests a potential for use in LTCC technology. © 2001 Elsevier Science Ltd. All rights reserved.

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1. Introduction

Pure tellurium dioxide is well known as a network-former in the glass industry, although pure tellurium dioxide does not form glass, even at high cooling rates.¹ Tellurium glasses exhibit a high refractive index and good optical transmission in the IR region, have interesting semiconducting properties and can be prepared at low temperatures.^{2,3} In contrast to glasses, tellurium-based oxide ceramics have not yet been seriously considered for use in electronics. Most tellurium-based oxide materials can be synthesised and sintered at temperatures below 900°C , which makes them potential candidates for use in low-temperature-cofired-ceramics (LTCC) technology. Other requirements for LTCC materials, in terms of their electrical properties, are high relative permittivity (κ'), high Q -value and a temperature coefficient of resonant frequency (τ_f) tunable around zero. For ceramic processing the most important oxidation states of tellurium are Te^{+4} and Te^{+6} , where Te^{+4} possesses a lone electron pair. In some cases, when

the thermodynamic conditions are fulfilled, an oxidation from Te^{+4} to Te^{+6} occurs in air. However, pure TeO_2 never oxidises in air to the $+6$ oxidation state.⁴

The highly temperature stable, tetragonal TeO_2 modification (space group P4_12_12), can be considered as a superstructure of rutile,^{4,5} with a duplicated c axis and unit-cell parameters of $a = 4.796 \text{ \AA}$ and $c = 7.626 \text{ \AA}$. The Te–O coordination polyhedra correspond to a heavily distorted quadratic bipyramid and the distances between the tellurium and oxygen ions are $2 \times 1.91 \text{ \AA}$, $2 \times 2.09 \text{ \AA}$ and $2 \times 2.89 \text{ \AA}$. Like TeO_2 , the rutile also TiO_2 crystallises in the tetragonal crystal system^{5,6} (space group P4/mnm) with unit-cell parameters of $a = 4.594 \text{ \AA}$ and $c = 2.959 \text{ \AA}$ and a Ti ion coordinated with 6 oxygens.

Only one compound on the TiO_2 – TeO_2 tie line is thermodynamically stable in air: TiTe_3O_8 with the tellurium in the $+4$ oxidation state.⁷ Many authors^{4,6–9} have already reported on the synthesis of the TiTe_3O_8 compound with a cubic unit cell, prepared from oxides at 700°C in air. Yamaguchi et al.¹⁰ have reported on the synthesis of another hexagonal modification prepared from amorphous precipitates which is irreversibly converted to the cubic modification at 520 – 570°C . Maeda et al.⁹ have reported microwave-dielectric properties of

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some tellurium ceramics: a relative permittivity of 36, a $Q \times f$ of 10,200 GHz and a temperature coefficient of relative permittivity (τ_ϵ) of -220 ppm/ $^\circ\text{C}$, measured at 4 GHz, were reported for cubic TiTe_3O_8 ceramics with 12% porosity.

The aim of the present study is to characterise the dielectric properties of the compositions from the TiO_2 – TeO_2 tie line. In addition, a study of the influence of the processing parameters on the dielectric properties of single-phase TiTe_3O_8 ceramics was performed. Because TeO_2 displays a negative temperature coefficient of resonant frequency and is chemically compatible with the TiTe_3O_8 compound we attempted to compensate the positive temperature coefficient of TiTe_3O_8 by an addition of TeO_2 and to determine its influence on the relative permittivity and $Q \times f$ -value.

2. Experimental

Ceramic samples have been prepared from reagent-grade TeO_2 (Alfa Aesar, 99.999%, lot I15J04) and TiO_2 (Johnson Matthey 99%, lot D17H27) via a solid-state-reaction method. The powders were weighed in different molar ratios, mixed in alcohol, dried and calcined for 80 h at 620 – 700°C with intermediate crushing until phase equilibrium was achieved. X-ray diffraction analysis (XRD) using a Philips PW 1710 X-ray powder diffractometer and CuK_α radiation was used to monitor the degree of calcination. After the calcination the samples were milled for one hour in a planetary ball mill at 200 rpm using 3 mm ϕ zirconia balls. An analysis revealed a mean particle size below 1 μm measured by granulometer (Cilas 8050). Powders were isostatically pressed into pellets and sintered in air. For the investigation of possible solid solubilities, unit-cell parameters were determined from XRD patterns using LCLSQ¹¹ software. Microstructural analyses were performed on a scanning electron microscope (SEM) (Jeol 5800 equipped with LINK ISIS X-ray spectrometer). Investigations of structural defects have been carried out on a transmission electron microscope (TEM) (Jeol 2000

FX). The sintering curves were recorded with a dilatometer (Bähr).

Electrical properties were measured by a reflection-resonant-cavity method at ~ 5 GHz with a HP 8719C network analyzer. The temperature dependence of resonant frequency was determined in the temperature range between 20 and 60°C .

3. Results

3.1. Characterisation of TiTe_3O_8

A single-phase TiTe_3O_8 compound was synthesised by solid-state reaction in air. (Fig. 1c) The determined unit-cell parameter ($a = 10.953$ Å) corresponds well to the literature data.⁸

To prevent the possible evaporation of TeO_2 , samples were sintered in a closed aluminum crucible together with TeO_2 powder. TeO_2 powder was placed in a separate aluminum crucible to increase the partial pressure of TeO_2 and to suppress the evaporation from TiTe_3O_8 . Obtained weight losses were in the range of 0.3 wt.%. A typical microstructure of a ceramic sintered at 720°C for 5 h, is shown in Fig. 2.

The TiTe_3O_8 ceramics exhibit $\sim 5\%$ porosity and a grain size of 2–5 μm . Microwave-dielectric properties of these ceramics, measured at ~ 5 GHz, are a $Q \times f$ -value of 30,600 GHz, relative permittivity of 50 and a temperature coefficient of resonant frequency of $+133$ ppm/ $^\circ\text{C}$. The $Q \times f$ value and the relative permittivity of these ceramics are much higher than previously reported due to a significant reduction in the porosity.

Additional investigations have been undertaken to examine whether any further improvement in the dielectric properties can be obtained by an adjustment of the processing parameters. Different thermally induced effects like stresses, precipitates and structural

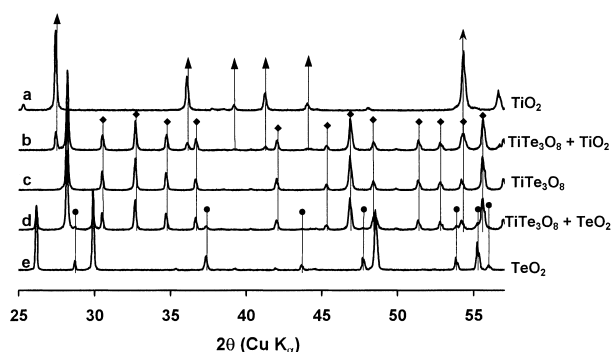


Fig. 1. XRD patterns of various samples on the TiO_2 – TeO_2 tie line.

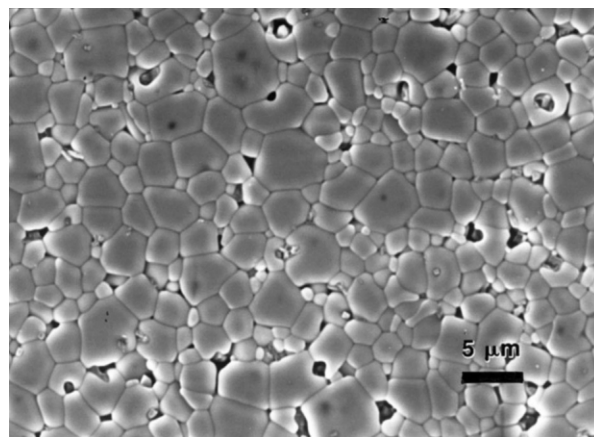


Fig. 2. Typical SEM image of the microstructure of a TiTe_3O_8 ceramic sintered at $720^\circ\text{C}/5$ h. The sample was thermally etched for 10 min at 710°C .

defects which can appear with the change in cooling rate, dwell time and sintering temperature, might have an influence on the dielectric properties of the ceramic. Investigations showed that neither a variation in the dwell time (5–15 h) nor the cooling rate (10–0.3°C/min) have an influence on the dielectric properties. Moreover, even variations in the sintering temperature in the range 720–750°C did not influence the dielectric properties. The only significant influence was observed when the sintering temperature was decreased too far for the successful densification of ceramics.

The apparent insensitivity of the TiTe_3O_8 ceramics to the firing conditions can be rationalised by the result of the TEM investigations, performed on a sample sintered at 720°C/5 h and cooled at 10°C/min. The TEM study (Fig. 3) revealed the presence of no structural defects such as inclusions, twins, precipitates, etc., which can be influenced by heat treatment conditions and subsequently reflected in the dielectric properties. Because of the regular structure of the TiTe_3O_8 compound further improvement in the dielectric properties of the TiTe_3O_8 ceramics can be expected only as a result of porosity elimination.

3.2. Characterisation of the TiTe_3O_8 – TeO_2 tie line

Tellurium and oxygen ions have a small difference in their electro-negativity (3.50 for oxygen and 2.01 for tellurium, according to Allred-Rochow), therefore, covalent bonding contributes significantly and hinders the sintering of pure TeO_2 . The sintering of milled, pure TeO_2 at 640°C for 15 h resulted in ceramics with ~20% porosity. Dielectric measurements, performed on such ceramics revealed a relative permittivity of 19.3 and a $Q \times f$ value of 30,000 GHz at ~4 GHz. Pure TeO_2 exhibits a negative temperature coefficient of resonant frequency

(–119 ppm/°C), therefore, it can be used to compensate for the positive temperature coefficient of TiTe_3O_8 . In accordance with the literature data,⁷ our XRD and SEM analyses confirmed the chemical compatibility of TiTe_3O_8 and TeO_2 (Figs. 1d and 4a) which is also important for the successful compensation of the temperature dependence of resonant frequency.

The unit-cell parameters of TeO_2 and TiTe_3O_8 phases in ceramics along the TeO_2 – TiTe_3O_8 tie line showed no variations with the composition. This suggests a negligible solid solubility of both compounds. These results are expected since the Te^{+4} ion with a stereoactive lone electron pair possesses a much larger ionic radius (0.97 Å for coordination number 6) than the Ti^{+4} ion (0.605 Å for coordination number 6), therefore, isovalent substitution is not very probable.

The sintering curve shows that ceramics with the composition 0.9 TiTe_3O_8 –0.1 TeO_2 start to sinter at temperatures around 600°C. Ceramics fired at 670°C were highly dense with an estimated porosity of less than 3%. Microwave-dielectric characteristics of the compositions from the TiTe_3O_8 – TeO_2 tie line are shown in Fig. 5.

The pure TiTe_3O_8 compound exhibits a τ_f of +133 ppm/°C. When the amount of TeO_2 compound in the system is increased the τ_f is reduced to +24 ppm/°C for the ceramic with a composition of 0.2 TiTe_3O_8 –0.8 TeO_2 and finally to –19 ppm/°C for 0.1 TiTe_3O_8 –0.9 TeO_2 . It is to be expected that the τ_f can be fully suppressed at approximately 0.15 TiTe_3O_8 –0.85 TeO_2 .

The relative permittivity of single-phase TiTe_3O_8 ceramics with ~5% porosity was determined to be 50 and to decrease with an increase in the concentration of the TeO_2 phase. The 0.2 TiTe_3O_8 –0.8 TeO_2 sample exhibits a relative permittivity of 34 and the 0.1 TiTe_3O_8 –0.9 TeO_2 sample has a relative permittivity of

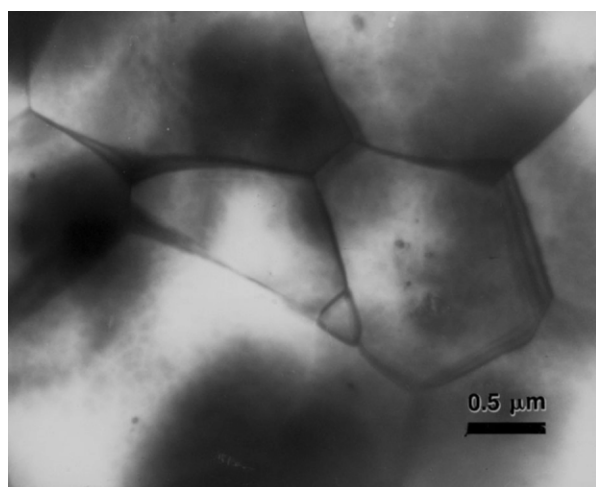


Fig. 3. Typical TEM image of a TiTe_3O_8 ceramic sintered at 720°C/5 h and cooled at 10°C/min. Micrograph reveals no main structural defects.

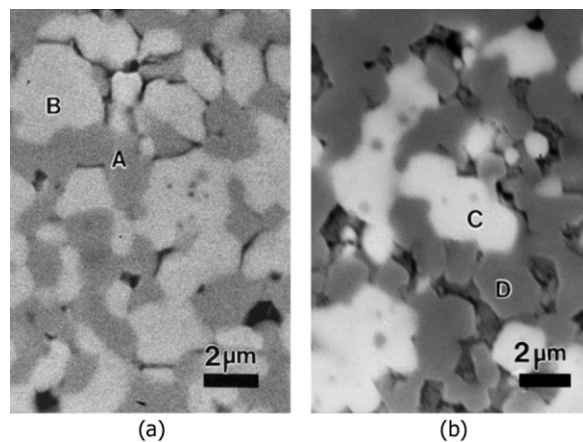


Fig. 4. (a) Typical back-scattered electron (BSE) image of a two-phase (Phase A: TiTe_3O_8 ; Phase B: TeO_2) dense ceramic with the composition 0.80 TiTe_3O_8 –0.2 TeO_2 . (b) Typical BSE image of two-phase (Phase C: TiTe_3O_8 ; Phase D: TeO_2) ceramic with the composition 0.6 TiO_2 –0.4 TeO_2 .

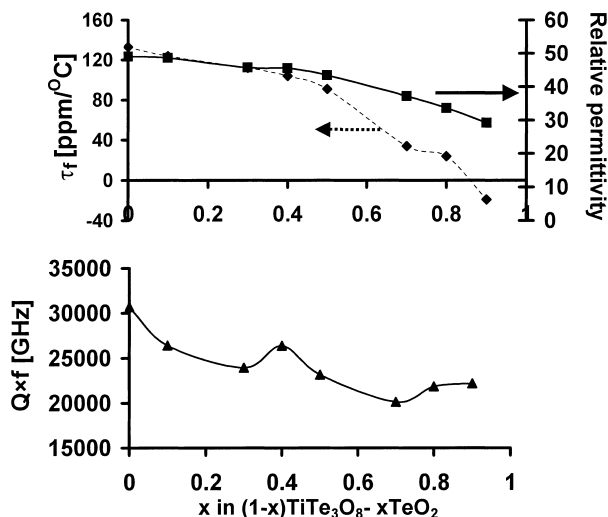


Fig. 5. Microwave dielectric properties of compositions from the TiTe_3O_8 – TeO_2 tie line.

29. The $Q \times f$ -value decreases from 30,600 GHz for single-phase TiTe_3O_8 to 22,000 GHz for the composition 0.2 TiTe_3O_8 –0.8 TeO_2 and remains the same for the 0.1 TiTe_3O_8 –0.9 TeO_2 sample.

3.3. Characterisation of the TiTe_3O_8 – TiO_2 tie line

SEM and XRD analyses of the 0.6 TiO_2 –0.4 TeO_2 sample (Fig. 1b) confirmed the literature data⁷ regarding the chemical compatibility of TiTe_3O_8 and TiO_2 . Cell-parameter determination of the 0.6 TiO_2 –0.4 TeO_2 sample indicates no changes in the unit-cell parameters, neither for the TiO_2 nor the TiTe_3O_8 phase, which again indicates a negligible solid solubility.

Fig. 4b shows a typical microstructure of ceramic with 0.6 TiO_2 –0.4 TeO_2 composition. The ceramic sample with this composition exhibits a relative permittivity of 62, a $Q \times f$ value of 23,000 GHz and a τ_f of +260 ppm/K. Both phases, TiO_2 and TiTe_3O_8 , possess positive temperature coefficients of resonant frequency, as a consequence the suppression of the temperature coefficient of resonant frequency is not possible.

4. Conclusions

TiTe_3O_8 is the only binary compound from the TiO_2 – TeO_2 tie line which is stable in air. Any solid solubility

between the compounds has not been detected and is also not very probable because of the large difference in the ionic radii of the titanium and tellurium ions. Single-phase TiTe_3O_8 ceramics with >95% theoretical density can be produced by sintering at 720°C in air. Measurements performed at ~5 GHz showed that such ceramics exhibit a relative permittivity of 50, a $Q \times f$ -value of 30,600 GHz and a positive temperature coefficient of resonant frequency of +133 ppm/°C. The temperature coefficient of resonant frequency of the TiTe_3O_8 compound can be compensated by the addition of ~85 mol% TeO_2 .

TeO_2 at ~4 GHz displays a relative permittivity of 19.3, a $Q \times f$ -value of 30,000 GHz and a temperature coefficient of resonant frequency of –119 ppm/°C. Ceramics with a composition 0.15 TiTe_3O_8 –0.85 TeO_2 , measured at ~5 GHz, exhibit a temperature coefficient of resonant frequency relative around 0, a permittivity ~30 and a $Q \times f$ -value of 22,000 GHz.

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